



NPN SURFACE MOUNT TRANSISTOR

Features

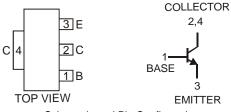
- **Epitaxial Planar Die Construction**
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)



SOT89-3L

Mechanical Data

- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking & Type Code Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.072 grams (approximate)



Schematic and Pin Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	25	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	Ic	5	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T _A = 25°C	P _D	1	W
Thermal Resistance, Junction to Ambient Air (Note 3) @T _A = 25°C	$R_{ heta JA}$	125	°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	°C

Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS (Note 4)						
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	25	_	_	V	$I_C = 10 \text{mA}, I_B = 0$
Collector Cut-off Current	I _{CBO}	_	_	1.0	μΑ	$V_{CB} = 50V, I_{E} = 0$
Emitter Cut-off Current	I _{EBO}	_	_	1.0	μА	$V_{EB} = 7.0V, I_{C} = 0$
ON CHARACTERISTICS (Note 4)			_		_	
Collector-Emitter Saturation Voltage	V	_	_	0.35		$I_C = 3.0A, I_B = 150mA$
Collector-Emitter Saturation voltage	V _{CE(SAT)}			0.50		$I_C = 4.0A$, $I_B = 200mA$
Base-Emitter Saturation Voltage	V			1.10		$I_C = 3.0A$, $I_B = 150mA$
Base-Emilier Saturation voltage	V _{BE(SAT)}			1.40		$I_C = 4.0A$, $I_B = 200mA$
		250		550		$I_C = 500 \text{mA}, V_{CE} = 2.0 \text{V}$
DC Current Gain	h _{FE}	150	_	_	_	$I_C = 2.0A$, $V_{CE} = 2.0V$
		50	50	_		$I_C = 5.0A$, $V_{CE} = 2.0V$
SMALL SIGNAL CHARACTERISTICS						
Current Gain-Bandwidth Product	f⊤	_	220	_	MHz	$I_C = 50 \text{mA}, V_{CE} = 6.0 \text{V},$ f = 100MHz
Output Capacitance	C _{obo}	_	_	50	pF	$V_{CB} = 10V, I_E = 0, f = 1MHz$

Notes:

- No purposefully added lead. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- Device mounted on FR-4 PCB; pad layout as shown on page 3 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 4. Measured under pulsed conditions. Pulse width = 300 µs. Duty cycle ≤2%.



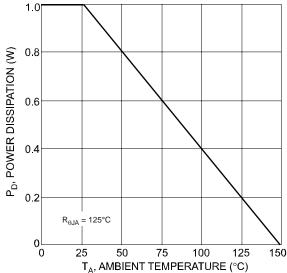


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 3)

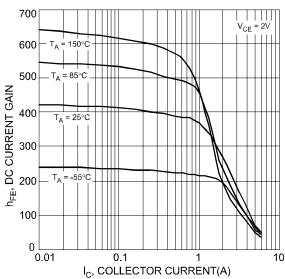


Fig. 3 Typical DC Current Gain vs. Collector Current

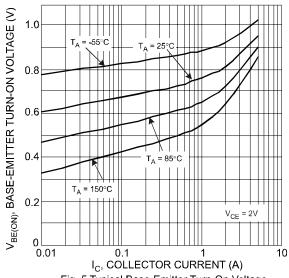


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

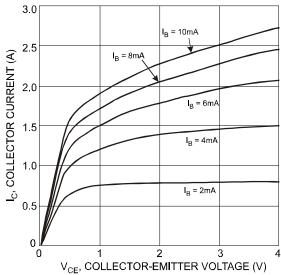


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

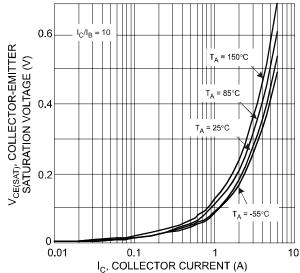
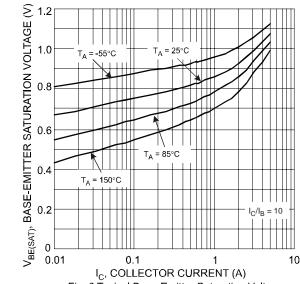


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current



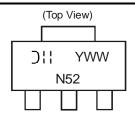


Ordering Information (Note 5)

Device	Packaging	Shipping
DXT3150-13	SOT89-3L	2500/Tape & Reel

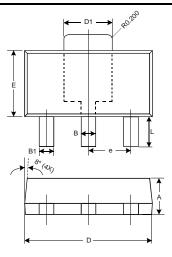
5. For packaging details, go to our website at http://www.diodes.com/ap02007.pdf.

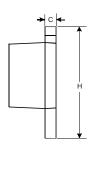
Marking Information



N52 = Product Type Marking Code YWW = Date Code Marking Y = Last digit of year ex: 7 = 2007 WW = Week code 01 - 52

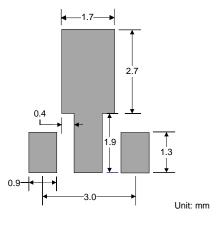
Package Outline Dimensions





SOT89-3L					
Dim	Min	Max	Тур		
Α	1.40	1.60	1.50		
В	0.45	0.55	0.50		
B1	0.37	0.47	0.42		
С	0.35	0.43	0.38		
D	4.40	4.60	4.50		
D1	1.50	1.70	1.60		
Е	2.40	2.60	2.50		
е			1.50		
Н	3.95	4.25	4.10		
L	0.90	1.20	1.05		
All Dimensions in mm					

Suggested Pad Layout



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